

## PATENT ABSTRACTS OF JAPAN

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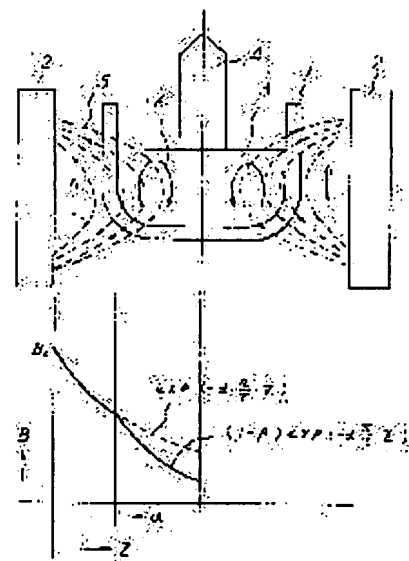
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## (54) PRODUCTION OF SINGLE CRYSTAL

## (57)Abstract:

PURPOSE: To stably obtain the title single crystal, by applying a vertical shifting magnetic field to the melt of a single crystal material in a crucible, and pulling up a single crystal while agitating the melt to uniformize the composition distribution as well as to uniformize the temp. distribution.

CONSTITUTION: The AC magnet 2 for generating a vertical shifting magnetic field is placed on the outside of the crucible 1, and the melt 3 of the single crystal material in the crucible 1 is vertically agitated by the vertical shifting magnetic field 5 based on the principle of a linear motor. A radial current is also induced by the vertical agitation to form an agitating current 6, hence the composition of the melt is uniformized by the agitation, and also the temp. is uniformized. By this method, the homogeneous semiconductor single crystal of Si, GaAs, etc., without having any flaw can be pulled up.



## LEGAL STATUS

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